PDTB123T series

PNP 500 mA, 50 V resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

Rev. 03 — 16 November 2009

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

Type number	Package		NPN complement	
	NXP	JEITA	JEDEC	
PDTB123TK	SOT346	SC-59A	TO-236	PDTD123TK
PDTB123TS[1]	SOT54	SC-43A	TO-92	PDTD123TS
PDTB123TT	SOT23	-	TO-236AB	PDTD123TT

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 500 mA output current capability
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs

- Cost-saving alternative for BC807 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current (DC)		-	-	-500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ



2. Pinning information

Table 3. **Pinning** Simplified outline Pin **Description Symbol** SOT54 1 input (base) 2 output (collector) 3 GND (emitter) 001aab347 SOT54A 1 input (base) 2 output (collector) 3 GND (emitter) R1 001aab348 006aaa217 **SOT54** variant 1 input (base) 2 output (collector) 3 GND (emitter) R1 001aab447 006aaa217 **SOT23; SOT346** 1 input (base) 3 2 GND (emitter) 3 output (collector) 2

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sym009

006aaa144

3. Ordering information

Table 4. Ordering information

Type number	Package			
	Name	Description	Version	
PDTB123TK	SC-59A	plastic surface mounted package; 3 leads	SOT346	
PDTB123TS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54	
PDTB123TT	-	plastic surface mounted package; 3 leads	SOT23	

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PDTB123TK	F1
PDTB123TS	TB123TS
PDTB123TT	*1U

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
V _I	input voltage				
	positive		-	+5	V
	negative		-	-12	V
I _O	output current (DC)		-	-500	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u>		
	SOT346		-	250	mW
	SOT54		-	500	mW
	SOT23		-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]			
	SOT346		-	-	500	K/W
	SOT54		-	-	250	K/W
	SOT23		-	-	500	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

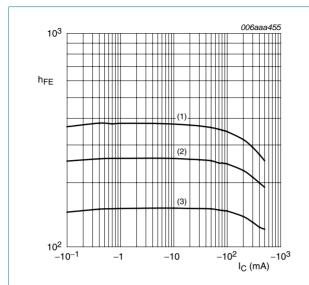
Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off	$V_{CB} = -40 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
	current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -50 \text{ V}; I_B = 0 \text{ A}$	-	-	-0.5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -50 \text{ mA}$	100	250	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -50 \text{ mA}; I_B = -2.5 \text{ mA}$	-	-	-0.3	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 100 MHz	-	11	-	pF

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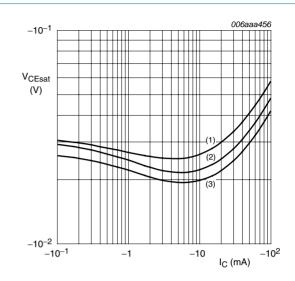
PNP 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

DC current gain as a function of collector Fig 1. current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

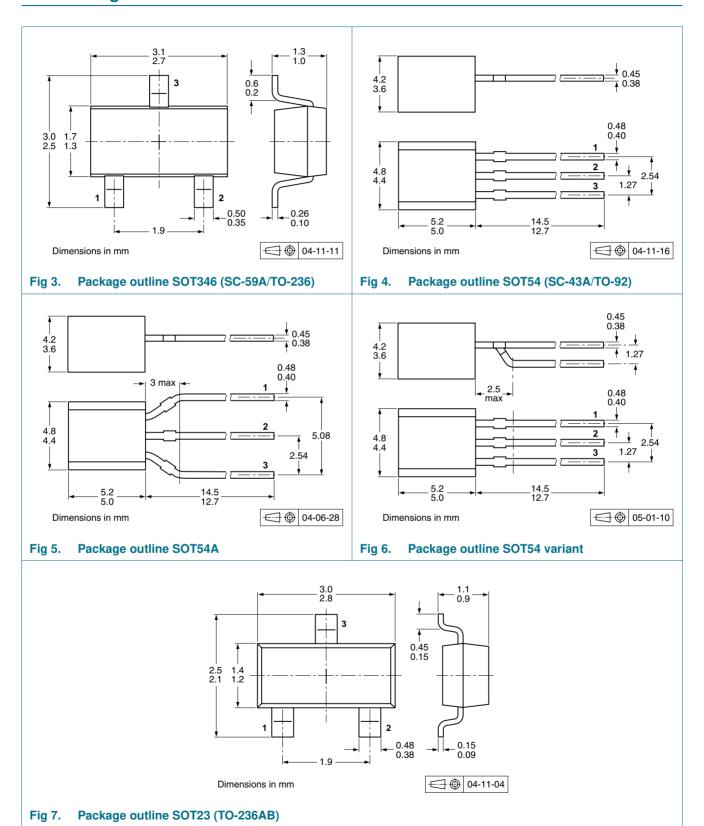
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Collector-emitter saturation voltage as a Fig 2. function of collector current; typical values

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PNP 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

8. Package outline



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PNP 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

Packing information 9.

Packing methods Table 9.

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
				5000	10000
PDTB123TK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTB123TS	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTB123TT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235

^[1] For further information and the availability of packing methods, see Section 12.



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PNP 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

10. Revision history

Table 10. Revision history

Product data sheet

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTB123T_SER_3	20091116	Product data sheet	-	PDTB123T_SER_2
Modifications:		eet was changed to reflect v legal definitions and disc		
PDTB123T_SER_2	20050804	Product data sheet	-	PDTB123TK_1
PDTB123TK_1	20050519	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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